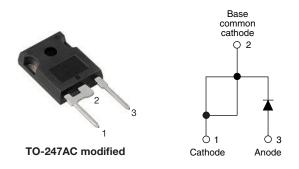
Vishay Semiconductors



Hyperfast Rectifier, 30 A FRED Pt®



PRODUCT SUMMARY					
Package	TO-247AC modified (2 pins)				
I _{F(AV)}	30 A				
V _R	600 V				
V _F at I _F	1.34 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Single diode device
- Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		600	V		
Average rectified forward current	I _{F(AV)}	T _C = 116 °C	30	٨		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	300	A		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-		
Forward voltage	V _F	I _F = 30 A	-	2.0	2.6	V	
Forward voltage V _F	vF	I _F = 30 A, T _J = 150 °C	-	1.34	1.75		
Deverse leekege eurrent		$V_{R} = V_{R}$ rated	-	0.3	50		
Reverse leakage current I _R		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	60	500	μA	
Junction capacitance	CT	V _R = 600 V	-	33	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	3.5	-	nH	





COMPLIANT HALOGEN

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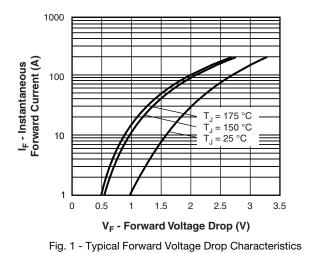


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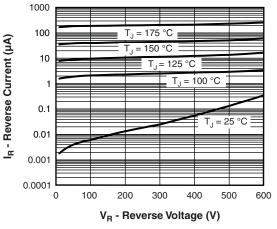
DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/μs, V _R = 30 V	-	28	35		
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 30 A dI _F /dt = 200 A/μs V _R = 200 V	-	31	-	ns	
		T _J = 125 °C		-	77	-		
Peak recovery current	I _{RRM}	T _J = 25 °C		-	3.5	-	А	
		T _J = 125 °C		-	7.7	-	~	
Deveree weeks weeks weeks		T _J = 25 °C		-	65	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	345	-	10	

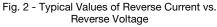
THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case per leg	R _{thJC}		-	0.5	0.9			
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.4	-			
Weight			-	6.0	-	g		
Weight			-	0.22	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-247AC modified		30EF	PH06			

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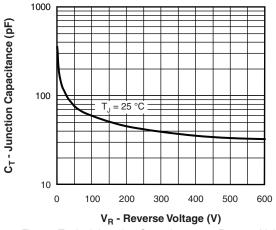


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

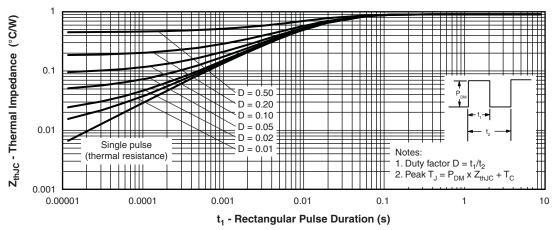


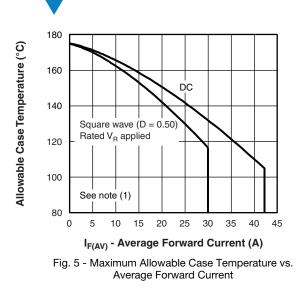
Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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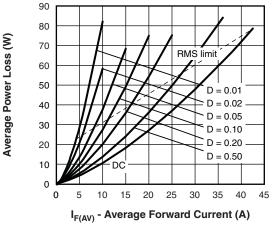


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \, x \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \ \mathsf{-D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

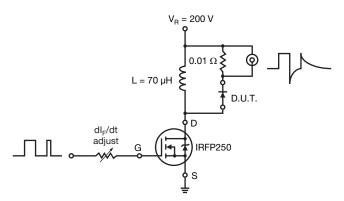


Fig. 9 - Reverse Recovery Parameter Test Circuit

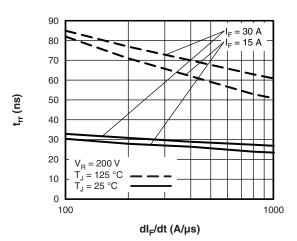


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

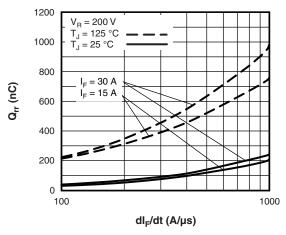
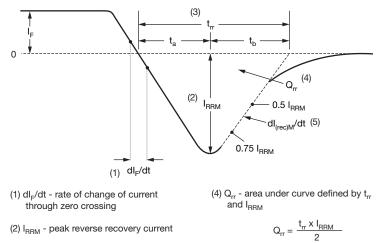


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device code	VS-	30	Е	Р	н	06	PbF
		2	3	4	5	6	7
	1	- Vis	hay Sen	nicondu	ctors pro	oduct	
	2	- Cur	rent rati	ng (30 =	= 30 A)		
	3	- Ciro	cuit conf	iguratio	n:		
		E =	single	diode			
	4	- Pao	ckage:				
		P =	TO-247	7AC mo	dified		
	5	- H=	hyperfa	ast recov	very		
	6	- Vol	tage rati	ing (06 =	= 600 V)	
	7 -	- Env	vironmer	ntal digit	:		
		PbF	= lead	(Pb)-fre	e and R	loHS-co	ompliant
		-N3	= halog	en-free	, RoHS-	complia	ant and

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-30EPH06PbF	25	500	Antistatic plastic tube				
VS-30EPH06-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95541			
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255			
	TO-247AC modified -N3	www.vishay.com/doc?95442			

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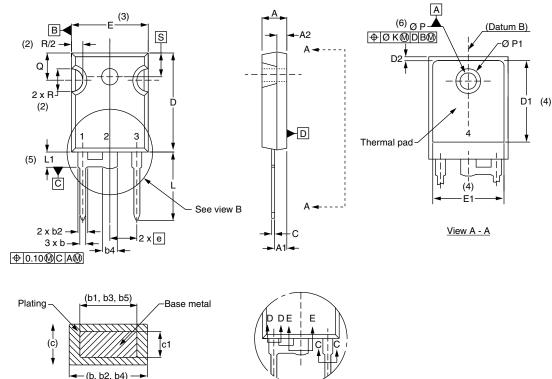
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TO-247AC modified - 50 mils L/F

DIMENSIONS in millimeters and inches



Section C - C, D - D, E - E

(4)

¦ E

View B

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INC	INCHES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215	BSC	
ØК	0.2	254	0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØP	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		SC 0.217 BSC		

Notes

- ⁽¹⁾ Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q

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